

PCS CDMA LOW NOISE AMPLIFIER/MIXER 1500MHz TO 2200MHz DOWNCONVERTER

RoHS Compliant & Pb-Free Product

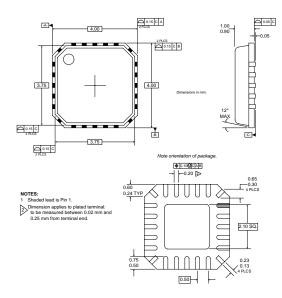
Typical Applications

- CDMA PCS Handsets
- GPS Receiver
- W-CDMA Handsets

- General Purpose Downconverter
- Commercial and Consumer Systems
- Portable Battery-Powered Equipment

Product Description

The RF2460 is a receiver front-end designed for the receive section of PCS CDMA and W-CDMA applications. It is designed to amplify and downconvert RF signals while providing 29dB of stepped gain control range and features digital control of LNA gain, mixer gain, and power down mode. A further feature of the chip is adjustable IIP3 of the LNA and mixer using an off-chip current setting resistor. Noise Figure, IP3, and other specs are designed to be compatible with the IS-98B for CDMA PCS communications. The IC is manufactured on an advanced Silicon Germanium Bi-CMOS process and is assembled in a 20-pin, QFN package with an exposed die flag.

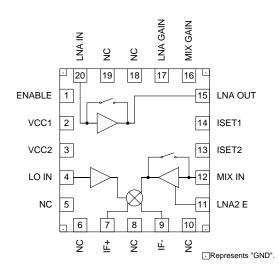


Package Style: QFN, 20-Pin, 4x4

Optimum Technology Matching® Applied

- ☐ Si BJT☐ Si Bi-CMOS
- ☐ GaAs HBT ☐ SiGe HBT
- ☐ GaAs MESFET☐ Si CMOS

- InGaP/HBT
- ☐ GaN HEMT
- SiGe Bi-CMOS



Functional Block Diagram

Features

- Complete Receiver Front-End
- Stepped LNA/Mixer Gain Control
- Adjustable LNA/Mixer Bias Current
- 24dB Gain and 2.2dB Noise Figure at Maximum Cascade Gain

Ordering Information

RF2460 MPCS CDMA Low Noise Amplifier/Mixer 1500 MHz

to 2200MHz Downconverter

RF2460PCBA-41X Fully Assembled Evaluation Board

 RF Micro Devices, Inc.
 Tel (336) 664 1233

 7628 Thorndike Road
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 Greensboro, NC 27409, USA
 http://www.rfmd.com

Absolute Maximum Ratings

Parameter	Rating	Unit
Supply Voltage	-0.5 to +5.0	V_{DC}
Input LO and RF Levels	+6	dBm
Operating Ambient Temperature	-40 to +85	°C
Storage Temperature	-40 to +150	°C



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Parameter	Specification			Unit	Condition	
Parameter	Min.	Тур.	Max.	Offic	Condition	
Overall					T=25°C, V _{CC} =2.75V, RF=1.96GHz,	
RF Frequency Range		1500 to 2200		MHz	LO=2170MHz@-7dBm, IF=210MHz	
LO Frequency Range		1200 to 2600		MHz		
IF Frequency Range		0.1 to 250		MHz		
Bias Current		2.5	2.8	mA	LNA, mixer and preamp for bias circuitry.	
US PCS - LNA		2.0	2.0	111/-3	ENA, mixer and preamp for bias circuity.	
Gain	13.5	15.0		dB		
Noise Figure	13.5	1.4	1.8	dВ		
Input IP3	+6.0	+7.0	1.0	dBm	IIP3 is adjustable (see plots for setting).	
input ii 3	10.0	17.0		dBiii	ISET1 (pin 14) external resistor sets current	
					consumption and performance.	
Input VSWR			2:1			
Output VSWR			2:1			
Current at Input IP3		7	7.5	mA		
US PCS - LNA Bypass						
Gain	-6	-5		dB		
Noise Figure		5	5.5	dB		
Input IP3	+23.0	+26.0		dBm		
Input VSWR			2:1			
Output VSWR			2:1			
Current		0		mA		
US PCS - Mixer - High Gain					1kΩ balanced load.	
Mode						
Gain	10	12		dB		
Noise Figure		6.5	7.5	dB		
Input IP3	+3.0	+4.0		dBm	IIP3 is adjustable (see plots for setting).	
RF to IF Isolation		>45		dB	ISET2 (pin 13) external resistor sets current	
					consumption and performance.	
Input VCM/D			2.1			
Input VSWR Output VSWR			2:1 2:1			
· ·		12	13	Λ		
Current US PCS - Mixer - Low Gain		12	13	mA	1kΩ balanced load.	
Mode					1 1/22 Dalai locu Idau.	
Gain	0	1.5		dB		
	U	_	16	-		
Noise Figure Input IP3	+13.0	15 +14.0	16	dB dBm	IIP3 is adjustable	
RF to IF Isolation	+13.0	+14.0 >45		dBm dB	ISET2 (pin 13) external resistor sets current	
IXI to II Isolatioff		240		UD	consumption and performance.	
Input VSWR			2:1			
Output VSWR			2:1			
Current		7.5	8.0	mA		

8-82 Rev B5 060921

Parameter	Specification			Unit	Condition	
Parameter	Min.	Тур.	Max.	Unit	Condition	
KPCS - LNA		·				
Gain	14.5	16.0		dB		
Noise Figure		1.4	1.8	dB		
Input IP3	+5.0	+6.0		dBm	IIP3 is adjustable (see plots for setting). ISET1 (pin 14) external resistor sets current consumption and performance.	
Input VSWR			2:1		' '	
Output VSWR			2:1			
Current at Input IP3		7	7.5	mA		
KPCS - LNA Bypass						
Gain	-6	-5		dB		
Noise Figure		5.0	5.5	dB		
Input IP3	+23.0	+26.0		dBm		
Input VSWR			2:1			
Output VSWR			2:1			
Current		0		mA		
KPCS - Mixer - High Gain					1kΩ balanced load.	
Mode						
Gain	10	12		dB		
Noise Figure		6.5	7.5	dB		
Input IP3	+2.5	+3.5		dBm	IIP3 is adjustable (see plots for setting).	
RF to IF Isolation		>45		dB	ISET2 (pin 13) external resistor sets current consumption and performance.	
Input VSWR			2:1			
Output VSWR			2:1			
Current		12	13	mA		
KPCS - Mixer - Low Gain					1 k Ω balanced load.	
Mode						
Gain	0	1.5		dB		
Noise Figure		15	16	dB		
Input IP3	+13.0	+14.0		dBm	IIP3 is adjustable	
RF to IF Isolation		>45		dB	ISET2 (pin 13) external resistor sets current	
					consumption and performance.	
Input VSWR			2:1			
Output VSWR			2:1			
Current		7.5	8.0	mA		

Davamatav		Specificatio	n	11::4	Condition	
Parameter	Min.	Тур.	Max.	Unit	Condition	
GPS - LNA						
Gain		16		dB		
Noise Figure		1.4		dB		
Input IP3		+7.0		dBm	IIP3 is adjustable. ISET1 (pin 14) external	
					resistor sets current consumption and perfor-	
		_			mance.	
Current at Input IP3 GPS - Mixer		7		mA	+	
		47		l n		
Gain		17		dB		
Noise Figure		6		dB	UD0: 11 . 1. 10=T(/ 1 . 4 / 1	
Input IP3		-5.0		dBm	IIP3 is adjustable. ISET1 (pin 14) external	
					resistor sets current consumption and performance.	
Current at Input IP3		16		mA	mance.	
GPS - Cascaded						
Gain		31		dB		
Noise Figure	1	1.8		dB		
Input IP3		-19.0		dBm	IIP3 is adjustable. ISET1 (pin 14) external	
put o					resistor sets current consumption and perfor-	
					mance.	
Current at Input IP3		23		mA		
Local Oscillator Input						
Input Level	-10	-7	0	dBm		
LO to RF Isolation		>40		dB	Any gain state.	
LO to LNA Isolation		>60		dB	Any gain state.	
LO Current Buffer		4.5	5.0	mA	I _{CC2} when LO signal is present	
US PCS - Cascade -					LNA High Gain/Mixer High Gain	
LNA High/Mixer High					Assuming 3dB loss of filter	
Gain		24		dB	IF 1, 1k Ω balanced load.	
Noise Figure		2.2		dB		
Input IP3		-8.0		dBm	Single sideband.	
Total Current		26		mA		
US PCS - Cascade -					LNA High Gain/Mixer Low Gain	
LNA High/Mixer Low					Assuming 3dB loss of filter	
Gain		13.5		dB	IF 1, 1k Ω balanced load.	
Noise Figure		5.3		dB		
Input IP3		+1.0		dBm	Single sideband.	
Total Current		21		mA		
US PCS - Cascade -					LNA Low Gain/Mixer High Gain Assuming 3dB loss of filter	
LNA Low/Mixer High					•	
Gain		4		dB	IF 1, 1k Ω balanced load.	
Noise Figure		14.5		dB		
Input IP3		+12.0		dB	Single sideband.	
Total Current		19		mA	LNA Low Gain/Mixer Low Gain	
US PCS - Cascade -					Assuming 3dB loss of filter	
LNA Low/Mixer Low						
Gain		-6.5		dB	IF 1, 1kΩ balanced load.	
Noise Figure		23		dB	Cinada aidab and	
Input IP3		+20.5		dB m^	Single sideband.	
Total Current		14		mA		

8-84 Rev B5 060921

Doromotor	Specification			11:4	O and distinct	
Parameter	Min.	Min. Typ. Ma		Unit	Condition	
KPCS - Cascade -					LNA High Gain/Mixer High Gain	
LNA High/Mixer High					Assuming 3dB loss of filter	
Gain		25		dB	IF 1, 1kΩ balanced load.	
Noise Figure		2.2		dB		
Input IP3		-9.5		dBm	Single sideband.	
Total Current		26		mA		
KPCS - Cascade -					LNA High Gain/Mixer Low Gain	
LNA High/Mixer Low					Assuming 3dB loss of filter	
Gain		14.5		dB	IF 1, 1kΩ balanced load.	
Noise Figure		5.3		dB		
Input IP3		+1.0		dBm	Single sideband.	
Total Current		21		mA		
KPCS - Cascade -					LNA Low Gain/Mixer High Gain	
LNA Low/Mixer High					Assuming 3dB loss of filter	
Gain		4		dB	IF 1, 1kΩ balanced load.	
Noise Figure		14.5		dB		
Input IP3		+12.0		dB	Single sideband.	
Total Current		19		mA		
KPCS - Cascade -					LNA Low Gain/Mixer Low Gain	
LNA Low/Mixer Low					Assuming 3dB loss of filter	
Gain		-6.5		dB	IF 1, 1kΩ balanced load.	
Noise Figure		23		dB		
Input IP3		+22		dB	Single sideband.	
Total Current		14		mA		
Power Supply						
Voltage	2.7	3.0	3.3	V		

Pin	Function	Description	Interface Schematic
1	ENABLE	Power down pin. A logic "low" turns the part off. A logic "high" (>1.6V) turns the part on.	
2	VCC1	Supply Voltage for the LNA, mixer, bias, and logic circuitry. External RF and IF bypassing is required. The trace length between the pin and the bypass capacitors should be minimized. The ground side of the bypass capacitors should connect immediately to ground plane.	See pin 20.
3	VCC2	Supply Voltage for the LO buffer amplifier. External RF and IF bypassing is required. The trace length between the pin and the bypass capacitors should be minimized. The ground side of the bypass capacitors should connect immediately to ground plane.	
4	LO IN	Mixer LO Input Pin.	
5	NC	No connection. For isolation purposes, this pin is connected to the ground plane.	
6	NC	No connection. For isolation purposes, this pin is connected to the ground plane.	
7	IF+	CDMA IF Output pin. This is a balanced output. The internal circuitry, in conjunction with an external matching/bias inductor to V_{CC} , sets the operating impedance. This inductor is typically incorporated in the matching network between the output and IF filter. The part is designed to drive a $1\mathrm{k}\Omega$ load. Because this pin is biased to V_{CC} , a DC blocking capacitor must be used if the IF filter input has a DC path to ground. See Application Schematic.	1.2 pF 1.2 pF
8	NC	No connection. For isolation purposes, this pin is connected to the ground plane.	
9	IF-	Same as pin 7, except complementary output.	See pin 6.
10	NC	No connection. For isolation purposes, this pin is connected to the ground plane.	
11	LNA2 E	Emitter for LNA2. Increasing the inductance on this pin will reduce the mixer gain, increase IP3 and noise figure.	
12	MIX IN	Mixer RF Input Pin. This pin is internally DC biased and should be DC blocked if connected to a device with DC present. External matching network sets RF and IF impedance for optimum performance.	MIX INO—
13	ISET2	This pin is used to set the bias current and IIP3 of the mixer amplifier using a resistor to ground. See plots for values and current settings.	
14	ISET1	This pin is used to set the bias current and IIP3 of the LNA amplifier using a resistor to ground. See plots for values and current settings.	
15	LNA OUT	LNA output pin. Open collector.	See pin 20.
16	MIX GAIN	CMOS compatible signal controlling mixer gain mode. Setting this signal high places the mixer in the high gain mode. Setting this signal low places the mixer in low gain mode by bypassing and shutting off the mixer buffer amplifier current.	MIX GAIN O-
17	LNA GAIN	CMOS compatible signal controlling LNA gain mode. Setting this signal high places the LNA in the high gain mode. Setting this signal low bypasses the LNA and shuts off the LNA bias current.	LNA GAIN O————
18	NC	No connection. For isolation purposes, this pin is connected to the ground plane.	
19	NC	No connection. For isolation purposes, this pin is connected to the ground plane.	

8-86 Rev B5 060921

Pin	Function	Description	Interface Schematic
20	LNA IN	RF Input pin. This pin is internally matched for optimum noise figure from a 50Ω source.	LNA IN O
Pkg Base	GND	Ground connection. The backside of the package should be soldered to a top side ground pad which is connected to the ground plane with multiple vias.	

Output Interface Network of the Mixer

L1, C1, C2, and R form a current combiner which performs a differential to single-ended conversion at the IF frequency and sets the output impedance. In most cases, the resonance frequency is independent of R and can be set according to the following equation:

$$f_{IF} = \frac{1}{2\pi \sqrt{\frac{L1}{2}(C_1 + 2C_2 + C_{EQ})}}$$

Where C_{EQ} is the equivalent stray capacitance and capacitance looking into pins 7 and 9. An average value to use for C_{EQ} is 2.5pF.

R can then be used to set the output impedance according to the following equation:

$$R = \left(\frac{1}{4 \cdot R_{OUT}} - \frac{1}{R_P}\right)^{-1}$$

where R_{OUT} is the desired output impedance and R_P is the parasitic equivalent parallel resistance of L1.

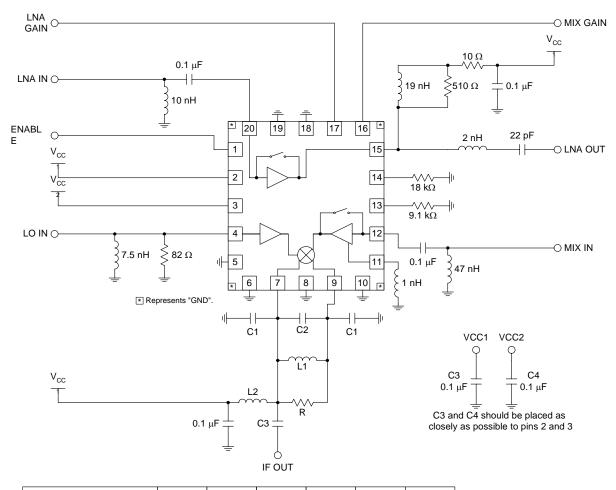
 C_2 should first be set to 0 and C1 should be chosen as high as possible (suggested less than 20pF), while maintaining an R_P of L1 that allows for the desired R_{OUT} . If the self-resonant frequencies of the selected C1 produce unsatisfactory linearity performance, their values may be reduced and compensated for by including C2 capacitor with a value chosen to maintain the desired F_{IF} frequency.

L2 and C3 serve dual purposes. L2 serves as an output bias choke, and C3 serves as a series DC block.

In addition, L2 and C3 may be chosen to form an impedance matching network if the input impedance of the IF filter is not equal to R_{OUT}. Otherwise, L2 is chosen to be large (suggested 120nH) and C3 is chosen to be large (suggested 22nF) if a DC path to ground is present in the IF filter, or omitted if the filter is DC blocked.

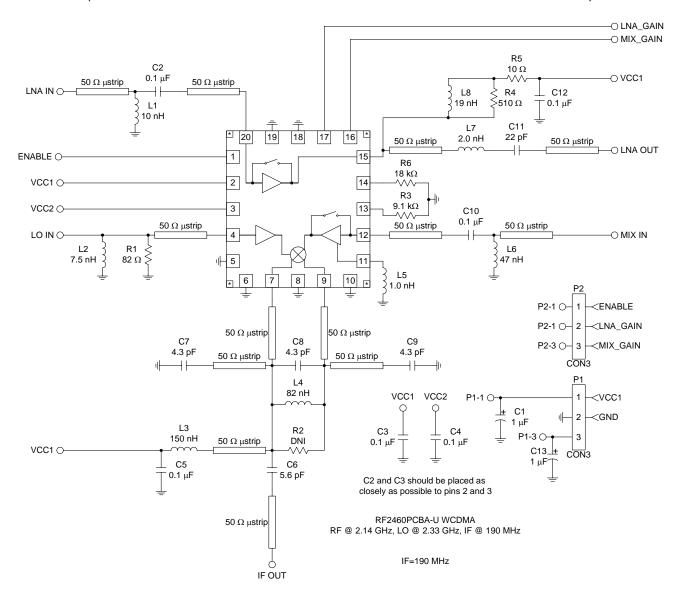
8-88 Rev B5 060921

Application Schematic - US PCS



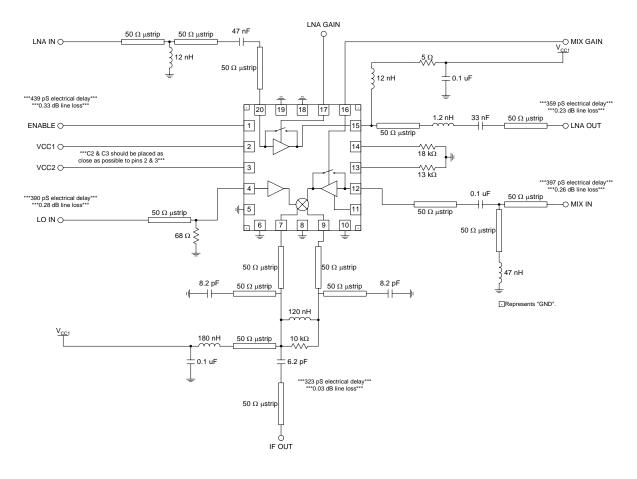
	C1 (pF)	C2 (pF)	C3 (pF)	L1 (nH)	L2 (nH)	R (Ω)
US PCS, IF = 210 MHz	4	3	6	82	110	4.7 k
Korean PCS, IF = 220 MHz	3.6	2	7	82	120	4.7 k
GPS, IF = 184 MHz	8.2	DNI	6.2	120	180	10 k
US PCS, IF = 184 MHz	8	3	6	82	110	4.7 k

Application Schematic - W-CDMA (See W-CDMA charts for lab measurements at the end of the data sheet)



8-90 Rev B5 060921

Application Schematic - GPS RF=1575MHz, IF=184MHz, LO=1759MHz



Current Measurement

To measure only the current of the different circuitry in the evaluation board, use the following procedure.

First, replace the bias choke inductor at the output of the mixer (L3 for US-PCS) with a 1Ω resistor. The voltage across the resistor will represent the mixer current. Terminate all SMA connections at 50Ω .

Second, follow the table below.

CONDITION

	Current (mA)	V _{CC1}	V _{CC2}	EN	LNA Gain	Mix Gain
I _{CC} Total	25.82	1	1	1	1	1
LNA Off	18.77	1	1	1	0	1
Mixer Preamp Off	14.28	1	1	1	0	0
V _{CC2} Off	10.05	1	0	1	0	0
Mixer Current	7.72	1	0	1	0	0

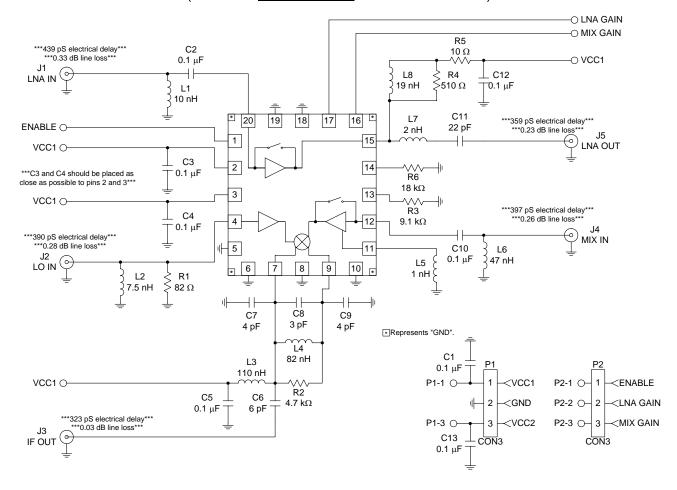
Therefore,

```
LNA (Bypass) = (Computer Simulation) =
                                                      0mA
  LNA (High Gain) =
                         25.82-18.77
                                                   7.05mA
   Mixer (Preamp) =
                         18.77-14.28
                                                   4.49mA
            Mixer =
                         (Measured)
                                                   7.70mA
             Bias =
                          10.05-7.7
                                                   2.35 mA
LO Circuitry (V<sub>CC2</sub>) =
                         14.28-10.05
                                                   4.23 mA
                                                  25.82mA
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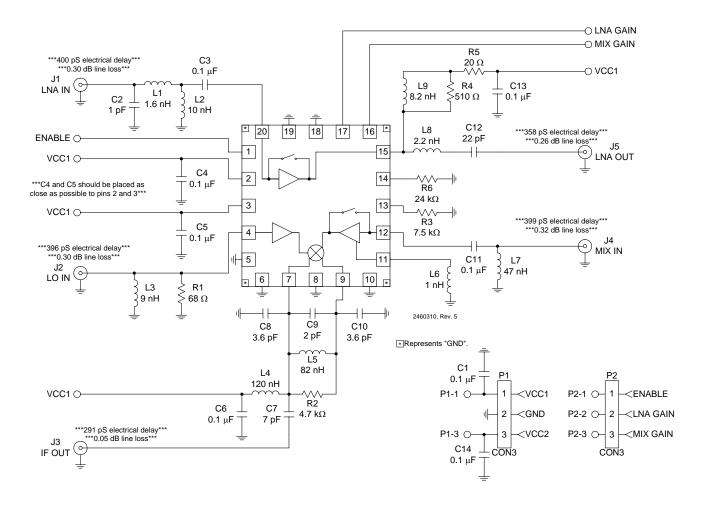
8-92 Rev B5 060921

Evaluation Board Schematic US-PCS, IF=210MHz

(Download Bill of Materials from www.rfmd.com.)



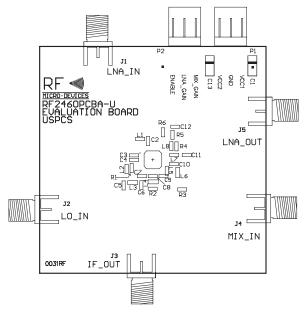
Evaluation Board Schematic Korean-PCS, IF=220MHz

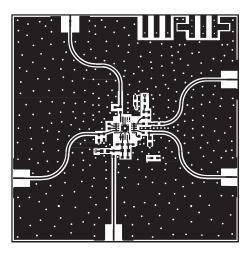


8-94 Rev B5 060921

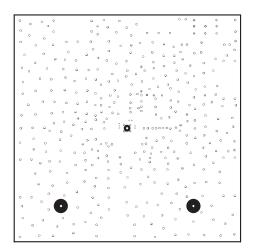
Evaluation Board Layout - US PCS Board Size 2.0" x 2.0"

Board Thickness 0.034", Board Material FR-4, Multi-Layer Assembly Top

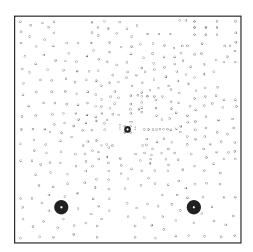




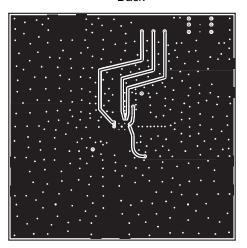
Power Plane 1



Power Plane 2

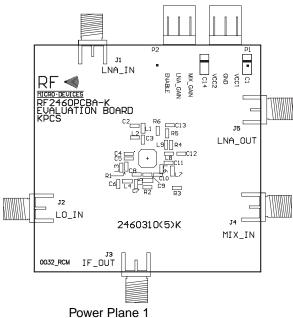


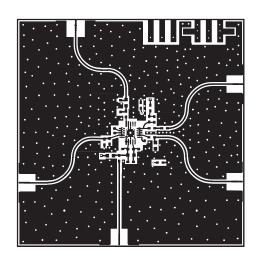
Back

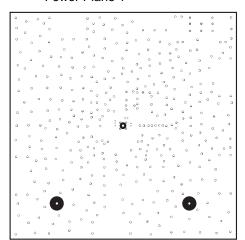


8-96 Rev B5 060921

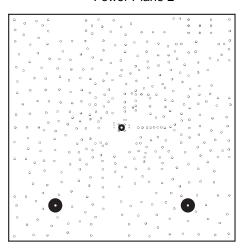
Evaluation Board Layout - Korean PCS $_{\mbox{\scriptsize Top}}$



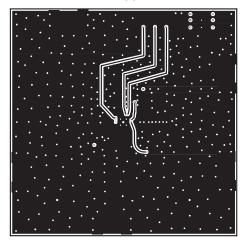




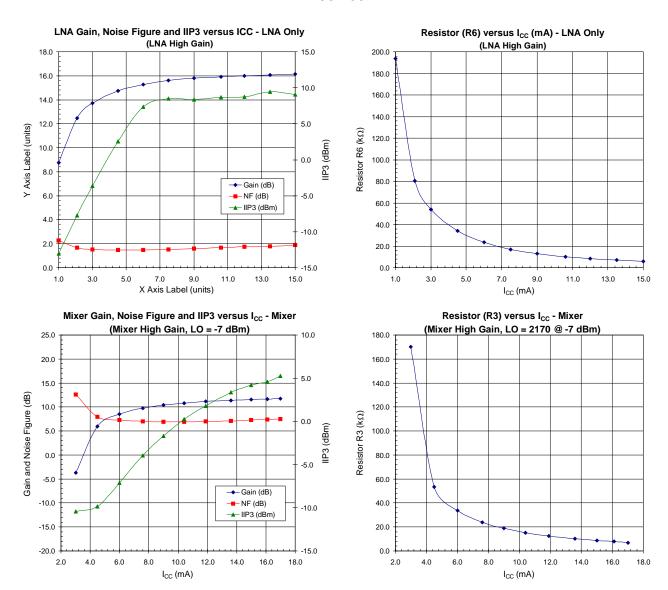
Power Plane 2



Back



US-PCS



Special Instructions (Board loss, taking into consideration description in the schematic)

<u>LNA</u>

V_{CC1}=V_{CC2}=Enable=2.75V; Mix Gain=0.0V

To measure I_{CC} LNA only:

LNA Gain was switched between 0V and 2.75V, and record the delta current.

<u>Mixer</u>

V_{CC1}=V_{CC2}=Enable=Mix Gain=2.75V; LNA Gain=0.0V

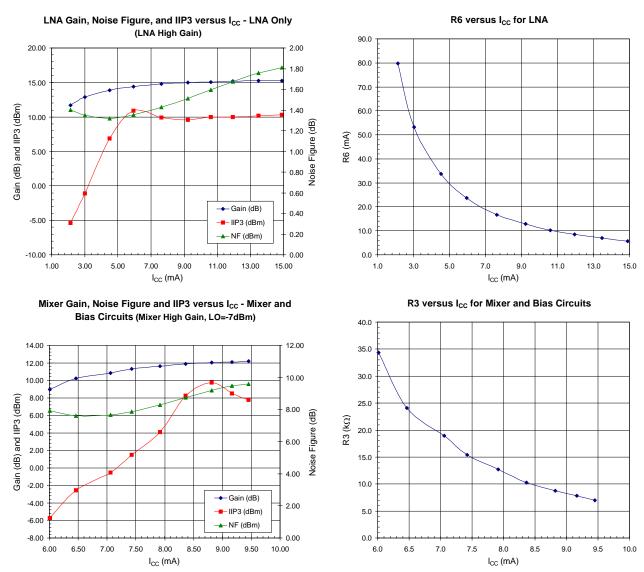
To measure I_{CC} Mixer (LNA should be in bypass mode and LO signal should be present):

Mixer Current=Total IC Current-LO Circuitry (~4.23mA) (See "Current Measurement" section for more details)

V_{CC2} only affects LO current buffer and R6 doesn't affect the mixer current.

8-98 Rev B5 060921

W-CDMA (See W-CDMA Application Schematic)



Instructions (Board loss, taking into consideration description in the W-CDMA schematic) LNA

 I_{CC} LNA current=total current (V_{CC} =LNA Gain=2.75)-total current (V_{CC} =2.75; LNA Gain=0) To measure I_{CC} LNA only:

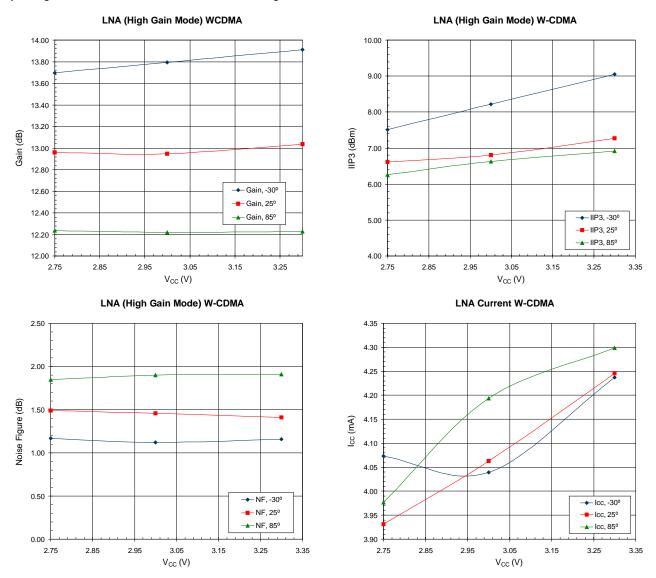
LNA Gain was switched between 0V and 2.75V, and record the delta current.

Mixer

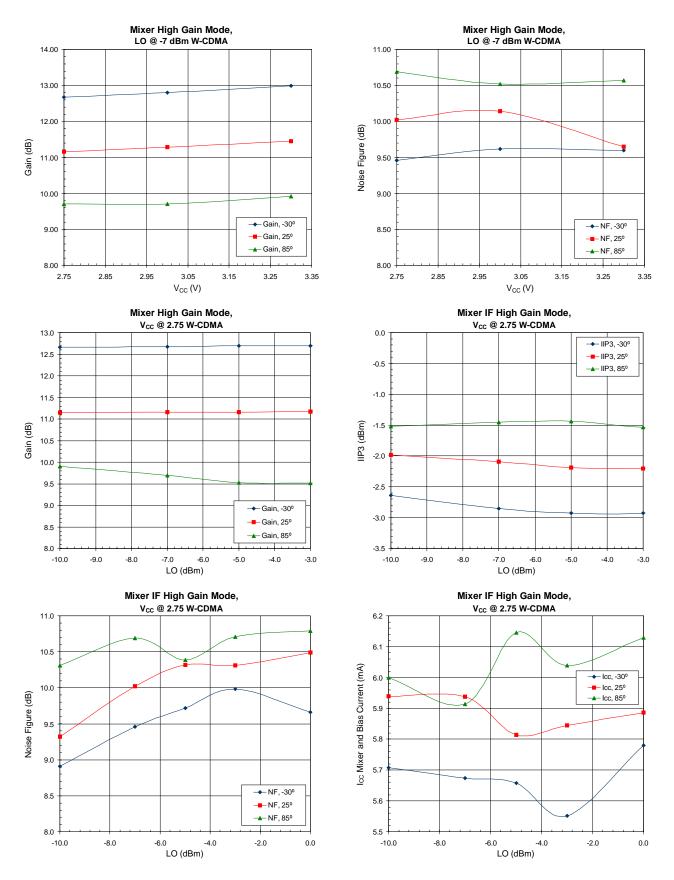
 I_{CC} Mix and Bias Current=Total Current (V_{CC1} =EN= V_{CC2} =Mix Gain=2.75; LNA Gain=0)-total current (V_{CC1} =EN=2.75; Mix Gain=LNA Gain= V_{CC2} =0)

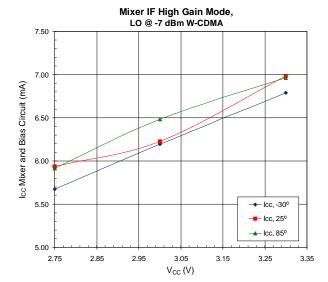
LO signal should be present. V_{CC2} only affects LO current buffer and R6 doesn't affect the mixer current.

By using a R6=39k Ω and R3=24k Ω , the following results were obtained. RF=2140MHz, LO=2330MHz, IF=190MHz.



8-100 Rev B5 060921





8-102 Rev B5 060921

PCB Design Requirements

PCB Surface Finish

The PCB surface finish used for RFMD's qualification process is electroless nickel, immersion gold. Typical thickness is 3µinch to 8µinch gold over 180µinch nickel.

PCB Land Pattern Recommendation

PCB land patterns are based on IPC-SM-782 standards when possible. The pad pattern shown has been developed and tested for optimized assembly at RFMD; however, it may require some modifications to address company specific assembly processes. The PCB land pattern has been developed to accommodate lead and package tolerances.

PCB Metal Land Pattern

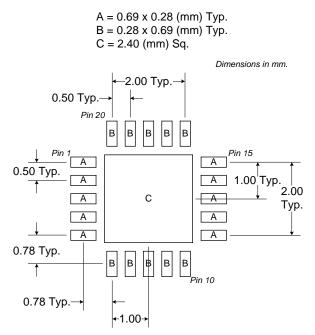


Figure 1. PCB Metal Land Pattern (Top View)

PCB Solder Mask Pattern

Liquid Photo-Imageable (LPI) solder mask is recommended. The solder mask footprint will match what is shown for the PCB metal land pattern with a 2mil to 3mil expansion to accommodate solder mask registration clearance around all pads. The center-grounding pad shall also have a solder mask clearance. Expansion of the pads to create solder mask clearance can be provided in the master data or requested from the PCB fabrication supplier.

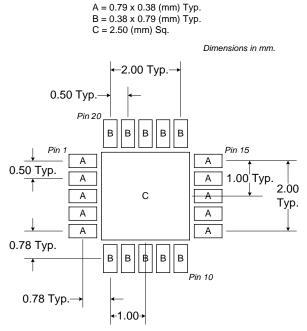


Figure 2. PCB Solder Mask Pattern (Top View)

Thermal Pad and Via Design

The PCB land pattern has been designed with a thermal pad that matches the die paddle size on the bottom of the device.

Thermal vias are required in the PCB layout to effectively conduct heat away from the package. The via pattern has been designed to address thermal, power dissipation and electrical requirements of the device as well as accommodating routing strategies.

The via pattern used for the RFMD qualification is based on thru-hole vias with 0.203mm to 0.330mm finished hole size on a 0.5mm to 1.2mm grid pattern with 0.025mm plating on via walls. If micro vias are used in a design, it is suggested that the quantity of vias be increased by a 4:1 ratio to achieve similar results.

8-104 Rev B5 060921